ROLL NO.

Code: AE53/AC53/AT53

**Time: 3 Hours** 

Subject: ELECTRONIC DEVICES & CIRCUITS

### AMIETE - ET/CS/IT

# JUNE 2014

Max. Marks: 100

PLEASE WRITE YOUR ROLL NO. AT THE SPACE PROVIDED ON EACH PAGE IMMEDIATELY AFTER RECEIVING THE QUESTION PAPER.

NOTE: There are 9 Questions in all.

- Question 1 is compulsory and carries 20 marks. Answer to Q.1 must be written in the space provided for it in the answer book supplied and nowhere else.
- The answer sheet for the Q.1 will be collected by the invigilator after 45 minutes of the commencement of the examination.
- Out of the remaining EIGHT Questions, answer any FIVE Questions. Each question carries 16 marks.
- Any required data not explicitly given, may be suitably assumed and stated.

# Q.1 Choose the correct or the best alternative in the following: (2×10) a. Energy band gap in pure germanium is \_\_\_\_\_

( <b>A</b> ) 1.1eV	<b>(B)</b> 0.5eV
( <b>C</b> ) 0.67eV	( <b>D</b> ) 1eV

b. In p-type material, the majority carriers and minority carriers are \_\_\_\_\_

(A) holes, electron	( <b>B</b> ) holes, neutron
(C) electron, neutron	<b>(D)</b> None of these

c. Most popular used transistor biasing circuit is\_\_\_\_\_

- (A) fixed bias(B) feedback bias(C) potential divider bias(D) None of these
- d. In multistage amplifier\_\_\_\_
  - $(\mathbf{A})$  Gain increases and BW increases
  - $({\bf B})$  Gain decreases and BW increases
  - (C) Gain decreases and BW decreases
  - $(\boldsymbol{D})$  Gain increases and BW decreases
- e. The change in output voltage from no load to full load condition is called\_\_\_\_\_

	<ul><li>(A) Rectification</li><li>(C) Efficiency</li></ul>	<ul><li>(B) Regulation</li><li>(D) Filtering</li></ul>
f.	f. An UJT can be used in the construction of	
	<ul><li>(A) an oscillator</li><li>(C) Both (A) &amp; (B)</li></ul>	<ul><li>(B) an amplifier</li><li>(D) a rectifier</li></ul>

g. For a SCR, the two transistor analogy holds good when the SCR is in \_\_\_\_\_

A) Forward blocking state	( <b>B</b> ) Condition state
<b>C</b> ) Both ( <b>A</b> ) & ( <b>B</b> )	( <b>D</b> ) None of these

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h. An amplifier has an open loop gain of 40dB and a bandwidth of 100kHz. Bandwidth need to increase 0.6MHz by providing suitable negative feedback. The amount of negative feedback should be\_\_\_\_\_

	<ul><li>(A) 0.5%</li><li>(C) 50%</li></ul>	<ul><li>(B) 0.05%</li><li>(D) 5%</li></ul>
i. Maximum efficiency of a Class-B push pull amplifier		
	<ul><li>(A) 75%</li><li>(C) 95%</li></ul>	<ul><li>(B) 50%</li><li>(D) 78.5%</li></ul>
j.	LSI technology includesn	number of gates on chip
	<ul><li>(A) less than 200</li><li>(C) more than 2000</li></ul>	<ul><li>(B) 200-2000</li><li>(D) None of these</li></ul>

#### Answer any FIVE Questions out of EIGHT Questions. Each question carries 16 marks.

Q.2 a. For the circuit shown in Fig.1, find the voltage across 2 mho conductance using Nodal analysis (8)



- b. State and explain the Norton and Reciprocity Theorem with one example of each. (8)
- **Q.3** a. A full-wave rectifier with a centre-tapped transformer supplies a dc current of 100mA to a load resistance of R=20 $\Omega$ . The secondary resistance of the transformer is 1 $\Omega$ , each diode has a forward resistance of 0.5 $\Omega$ . Determine the following:
  - (i) RMS value of signal voltage across each half of the secondary.
  - (ii) DC power supplied to the load.
  - (iii) PIV rating of each diode.
  - (iv) AC power input to the rectifier.
  - (v) Conversion efficiency.
  - (vi) Voltage regulation.

(8)

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- b. Compare performance of a halfwave rectifier, a centre tapped full wave rectifier and a bridge type full wave rectifier. (8)
- Q.4 a. Draw and explain the transfer characteristics of FETs. (8)
  - b. What are four layer devices? Explain the switching action of Silicon Controlled Rectifier (SCR). (8)
- Q.5 a. Explain the need of biasing in transistor circuit and determine the stability factor of fixed bias circuit.(8)
  - b. What is h-parameter model? Draw and explain a BJT h-parameter models. (8)
- Q.6 a. Draw & explain the circuit diagram and frequency response of a Single stage RC- coupled amplifier.
   (8)
  - b. A BJT transistor amplifier stage has  $R_E=R_C=1.5k\Omega$ ,  $R_S=600\Omega$ ,  $R_L=2k\Omega$  and transistor parameter  $\beta=100$  and  $r_{\pi}=1k\Omega$ . Determine the value of  $C_{C_1}$ ,  $C_{C_2}$  and  $C_E$  needed to obtain  $f_L=50Hz$  and also

draw

the circuit. (8)

**Q.7** a. In the ideal class-B amplifier with complimentary symmetry shown in figure having  $V_{CC}=15V$ ,  $R_L=10\Omega$ . The input is sinusoidal. Determine the maximum signal output power, the corresponding collector dissipation and conversion efficiency. (8)



Class-B amplifier with complimentary symmetry

#### Fig.2

- b. With the help of suitable diagram, explain the following: (8)
  (i) Class-C power amplifier (ii) Class-AB power amplifier
- Q.8 a. Explain Wein bridge Oscillator. (8)
  - b. What are the effect of negative feedback on gain and bandwidth of an amplifier? Explain.
     (8)

#### **Q.9** a. Explain photolithography masking and Etching. (6)

b. What is the width required to fabricate  $5k\Omega$  resistor whose length is  $25\mu$ m. Given  $R_S = 200\Omega/square$  (4)

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c. Briefly explain the steps involved in IC fabrication.

(6)

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